

L Number	Hits	Search Text	DB	Time stamp
-	46	low adj temperature near7 (silicon adj dioxide or silicon adj oxide) and (ultra adj violet or uv) and cvd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 13:51
-	3478	(silicon adj dioxide or silicon adj nitride) and atmospheric adj pressure and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 16:11
-	7835	noble adj gas	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 16:11
-	96	((silicon adj dioxide or silicon adj nitride) and atmospheric adj pressure and plasma) and (noble adj gas)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 16:55
-	1494	apcvd or "atmospheric pressure chemical vapor deposition"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 11:47
-	31	(noble adj gas) and (apcvd or "atmospheric pressure chemical vapor deposition")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 16:56
-	249	"90" adj kpa or "110" adj kpa	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:46
-	127583	argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:44
-	33	("90" adj kpa or "110" adj kpa) and argon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:44
-	274720	wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:46
-	11	("90" adj kpa or "110" adj kpa) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:46
-	1249	apcvd or "atmospheric pressure chemical vapor deposition" and ("90" adj kpa or "110" adj kpa)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 12:54
-	621	wafer and (apcvd or "atmospheric pressure chemical vapor deposition" and ("90" adj kpa or "110" adj kpa))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 17:50
-	62266	noble	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 12:55

-	31	(wafer and (apcvd or "atmospheric pressure chemical vapor deposition" and ("90" adj kpa or "110" adj kpa))) and noble	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/20 18:06
-	2	("5858819").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/20 18:06
-	25043	"100" adj kpa or "760" adj torr or "1" adj atm or "1" adj atmosphere or "760mm"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 11:47
-	1270	apcvd or "atmospheric pressure chemical vapor deposition" and ("100" adj kpa or "760" adj torr or "1" adj atm or "1" adj atmosphere or "760mm")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 11:47
-	47	noble and (apcvd or "atmospheric pressure chemical vapor deposition" and ("100" adj kpa or "760" adj torr or "1" adj atm or "1" adj atmosphere or "760mm"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 11:56
-	69	(atmospheric adj processing or atmospheric adj process) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:12
-	65	siniaguine.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:12
-	3781	ecr and semiconductor and (process or processing)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:45
-	4276	uv and noble	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:46
-	45	(ecr and semiconductor and (process or processing)) and (uv and noble)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:54
-	1252	apcvd or "atmospheric pressure chemical vapor deposition" and uv and rf	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:55
-	47	noble and (apcvd or "atmospheric pressure chemical vapor deposition" and uv and rf)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 12:55
-	14	low adj temperature near7 (silicon adj dioxide or silicon adj oxide) and (ultra adj violet or uv) and cvd and alloy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/09/21 13:52